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**PATENT**

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| Applicant(s): | Martin Hausner |
| Serial No.: | Unknown (National Phase of International Application PCT/EP03/09052) |
| Filed: | February 11, 2005 (Priority Date Claimed August 14, 2002) |
| Examiner: | Unknown |
| Group Art Unit: | Unknown |
| Confirmation No.: | Unknown |
| Title: | **METHOD FOR SELECTIVELY REMOVING MATERIAL FROM THE SURFACE OF A SUBSTRATE, MASKING MATERIAL FOR A WAFER, AND WAFER WITH MASKING MATERIAL** |
| Our Ref. No.: | BEET-09 |

Cincinnati, Ohio 45202 February 11, 2005

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Sir:

**INFORMATION DISCLOSURE STATEMENT**

In accordance with the duty of candor and good faith imposed by 37 C.F.R. §1.56 and means of complying therewith according to 37 C.F.R. §§1.97 and 1.98, the references listed on the attached Form PTO-1449 are called to the

attention of the United States Patent and Trademark Office in connection with the above-identified patent application. Because the requirement (37 C.F.R. §1.98(a)(2)(i)) for submitting copies of U.S. patents and published applications has been waived, copies of only the foreign cited references and/or other documents are enclosed herewith.

No representation is made that the cited art is the only art or that the cited art represents the best art.

The Examiner is urged to consider all of the cited documents and to make an independent evaluation of the teachings and materiality of each.

No fees are believed to be due. However, if any additional fees are necessary to complete this communication, please apply them to Deposit Account No. 23-3000.

Respectfully submitted,

WOOD, HERRON & EVANS, L.L.P.

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| INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (37 CFR 1.98(b)) | | APPLICANT Martin Hausner | |
| | | FILING DATE February 11, 2005 | GROUP Unknown |

U.S. PATENT DOCUMENTS

| EXAMINER INITIAL | | PATENT NUMBER | ISSUE DATE | PATENTEE | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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| EXAMINER INITIAL | | PATENT NUMBER | ISSUE DATE | PATENTEE | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE |
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